



PATENT ABSTRACTS OF JAPAN

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aoyama tetsuo****(54) METHOD FOR REMOVING PHOTORESIST****(57) Abstract:**

PROBLEM TO BE SOLVED: To provide a method for removing a photoresist by which the remaining photoresist in the photolithographic process of forming a pattern on the metal face of an electronic material such as a lead frame, printed wiring board or the like can be removed in a short time without deforming the

metal pattern.

SOLUTION: The removing liquid used in the method consists of an aqueous solution containing a quaternary ammonium hydroxide, water-soluble amines, hydroxyl amines, and if necessary, a corrosion preventive agent for copper-based metals.

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